







Application

Laser Projector Measuring equipment

Property

Wavelength λ = 660 nm Output Power = 50mW Package Type = ϕ 5.6mm

Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipment, medical instruments and aerospace applications.

Red Laser Diode Key features

Absolute Maximum Rating at Tc=25℃

Items	Symbols	Values	Unit
Operating Current power	P。	50	mW
Reverse Voltage LD	V_{R}	2	V
Operating Temperature	T_{case}	-10~+70	$^{\circ}\! \mathbb{C}$
Storage Temperature	T_s	-40~+85	$^{\circ}\!\mathbb{C}$



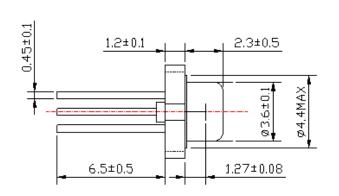


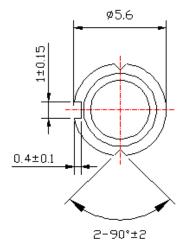
660nm RED Laser Diode

Electrical and Optical Characteristics at Tc=25℃

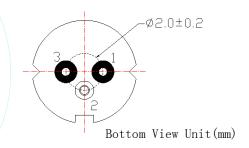
ltem	Symbols	Min	Тур.	Max.	Unit	Condition
Threshold Current	I_{th}	-	45	60	mA	-
Operating Current	I_{op}	-	90	120	mA	Po=50mW
Operating Voltage	V_{op}	-	2.6	3	V	Po=50mW
Peak Wavelength	λр	640	650	665	nm	Po=50mW
Beam Divergence (FWHM)	$\theta_{/\!\!/}$	6	9	13	deg	Po=50mW
Beam Divergence (FWHM)	$ heta$ \perp	15	20	25	deg	Po=50mW
Monitor Current	I_{m}	0.05	0.3	1	mA	Po=50mW

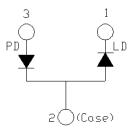
Package Drawing





ELECTRICAL CONNECTION





Specifications are subject to change without notice.





